

RF POWER TRANSISTOR

DESCRIPTION:

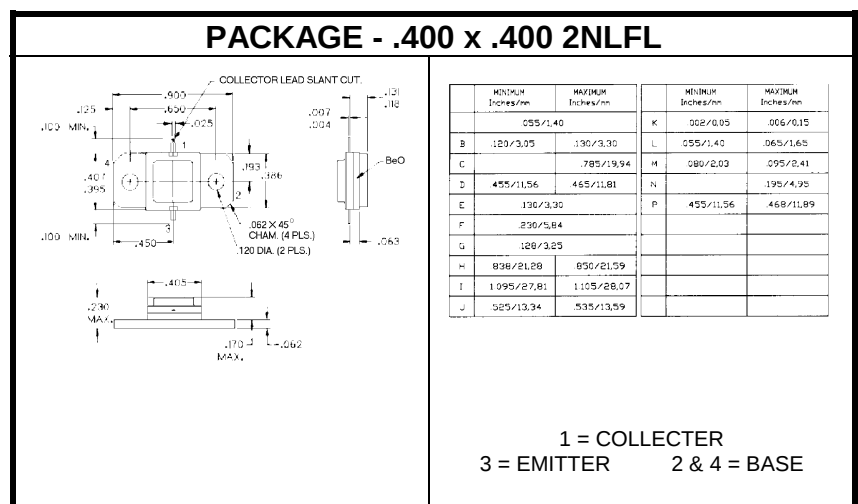
The **ASI 1214-6** is a Common Base Transistor Designed for Long Pulse High Reliability L-Band Radar Applications.

FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	55 V
P_{DISS}	125 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.4 °C/W



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 20 mA	55			V
BV_{CER}	I _C = 40 mA R _{BE} = 10 Ω	55			V
BV_{EBO}	I _E = 2.0 mA	3.5			V
I_{CES}	V _{CE} = 28 V			10	mA
h_{FE}	V _{CE} = 5.0 V I _C = 2.0 A	15		150	---
P_G	V _{CC} = 28 V P _{OUT} = 55 W f = 1214 to 1400 MHz	6.6	7.2		dB
η_C	Pulse Width = 1000 μS Duty Cycle = 10%	50	55		%